

CDBDSC6650-G

Reverse Voltage: 650 V

Forward Current: 6 A

RoHS Device

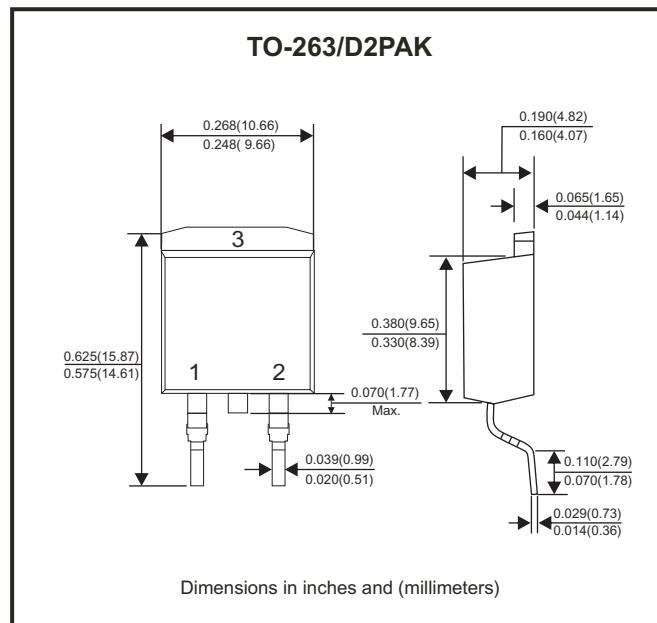


Features

- Rated to 650V at 6 Amps
- Zero reverse recovery current
- Zero forward recovery voltage
- Temperature independent switching behaviour.
- High temperature operation.
- High frequency operation.

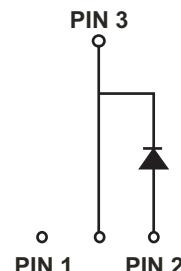
Mechanical data

- Case: TO-263/D2PAK, molded plastic.
- Terminals: Solderable per MIL-STD-750, method 2026.



Dimensions in inches and (millimeters)

Circuit Diagram



Maximum Ratings (at $T_A=25^\circ\text{C}$, unless otherwise noted)

Parameter	Conditions	Symbol	Limit	Unit
Repetitive peak reverse voltage	$T_j = 25^\circ\text{C}$	V_{RRM}	650	V
Surge peak reverse voltage	$T_j = 25^\circ\text{C}$	V_{RSM}	650	V
DC bolcking voltage	$T_j = 25^\circ\text{C}$	V_{DC}	650	V
Continuous forward current	$T_c = 25^\circ\text{C}$ $T_c = 135^\circ\text{C}$ $T_c = 158^\circ\text{C}$	I_F	21.5 10 6	A
Repetitive peak forward surge current	$T_c = 25^\circ\text{C}$, $t_p = 10\text{ms}$ Half sine wave, $D = 0.3$	I_{FRM}	30	A
Non-repetitive peak forward surge current	$T_c = 25^\circ\text{C}$, $t_p = 10\text{ms}$ Half sine wave	I_{FSM}	42	A
Power dissipation	$T_c = 25^\circ\text{C}$	P_{TOT}	85.8	W
	$T_c = 110^\circ\text{C}$		39	
Typical thermal resistance	Junction to case	$R_{\theta JC}$	1.748	$^\circ\text{C}/\text{W}$
Operating junction temperature range		T_J	-55 ~ +175	$^\circ\text{C}$
Storage temperature range		T_{STG}	-55 ~ +175	$^\circ\text{C}$

Silicon Carbide Power Schottky Diode

Comchip
SMD Diode Specialist

Electrical Characteristics (at $T_A=25^\circ\text{C}$, unless otherwise noted)

Parameter	Conditions	Symbol	Min.	Typ.	Max.	Unit
Forward voltage	$I_F = 6\text{A}, T_j = 25^\circ\text{C}$	V_F		1.44	1.8	V
	$I_F = 6\text{A}, T_j = 175^\circ\text{C}$			1.73	2.5	
Reverse current	$V_R = 650\text{V}, T_j = 25^\circ\text{C}$	I_R		10	100	μA
	$V_R = 650\text{V}, T_j = 175^\circ\text{C}$			15	200	
Total capacitive charge	$V_R = 400\text{V}, T_j = 150^\circ\text{C}$ $Q_C = \int_0^{V_R} C(V) dV$	Q_C		23		nC
Total capacitance	$V_R = 0\text{V}, T_j = 25^\circ\text{C}, f = 1\text{MHz}$	C		424	434	pF
	$V_R = 200\text{V}, T_j = 25^\circ\text{C}, f = 1\text{MHz}$			44	45	
	$V_R = 400\text{V}, T_j = 25^\circ\text{C}, f = 1\text{MHz}$			42.5	43	

RATING AND CHARACTERISTIC CURVES (CDBDSC6650-G)

Fig.1 - Forward Characteristics

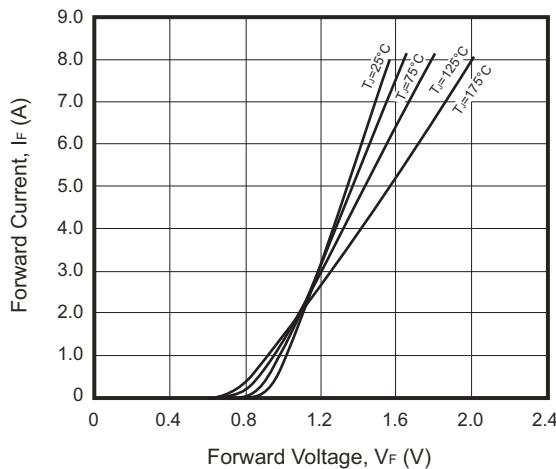


Fig.2 - Reverse Characteristics

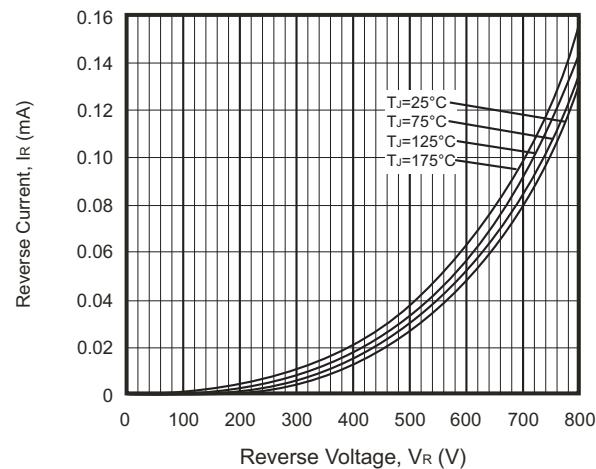


Fig.3 - Current Derating

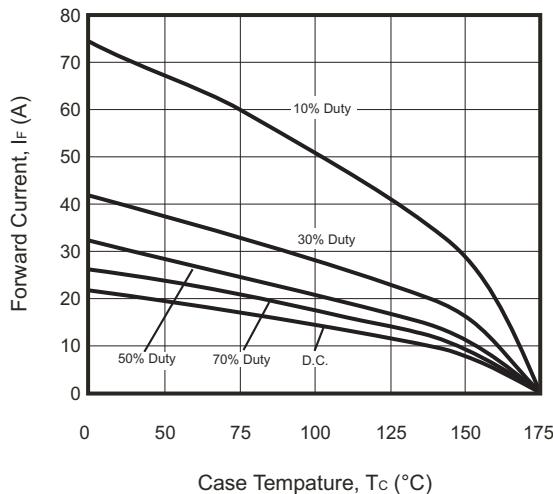
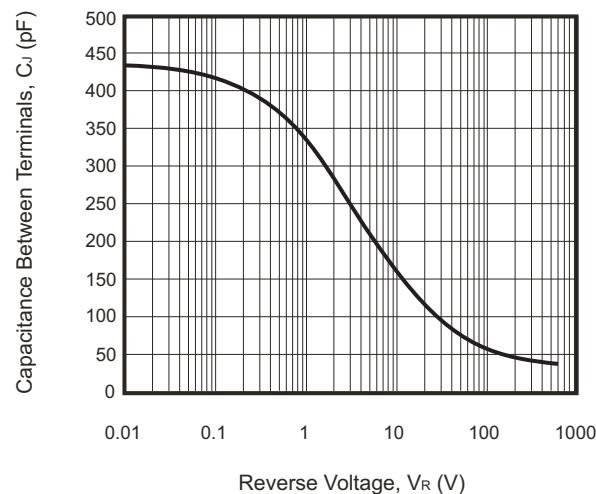
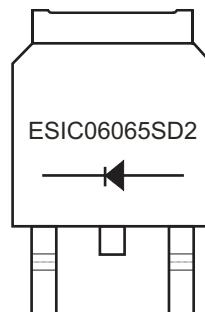


Fig.4 - Capacitance Characteristics



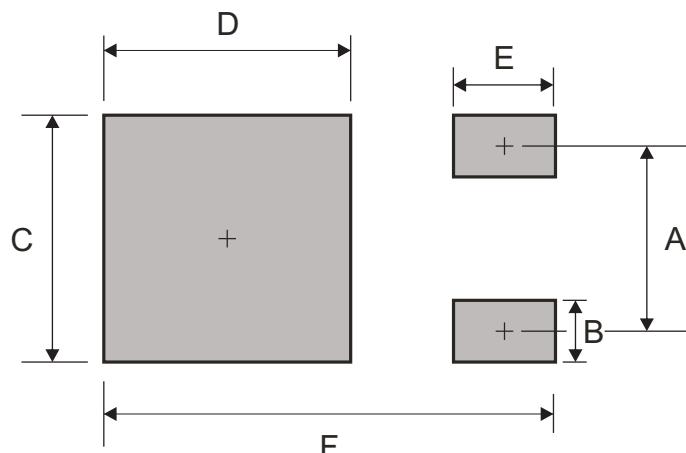
Marking Code

Part Number	Marking Code
CDBDSC6650-G	ESIC06065SD2



Suggested PAD Layout

SIZE	TO-263 / D2PAK	
	(mm)	(inch)
A	5.08	0.200
B	1.10	0.043
C	10.80	0.425
D	8.30	0.327
E	3.50	0.138
F	16.90	0.666



Standard Packaging

Case Type	TUBE PACK	
	TUBE (pcs)	CARTON (pcs)
TO-263 / D2PAK	50	4,000